

Diodes | $I_o = I_s(e^{v_{DN}/V_t} - 1) \rightarrow I_s \approx 10^{-14}, 10^{-15} A$ | Note down assumptions / $V_p = \sqrt{2} V_{rms}$

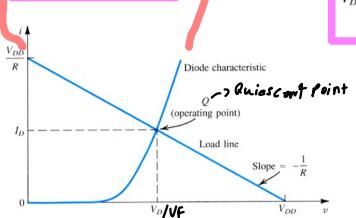
Exponential Model

$$I_{D0} = I_s e^{v_{DN}/V_t}$$

$$I_{D0} = I_s e^{v_{DN}/V_t} \rightarrow v_{D0} = V_{D0} + V_t \ln\left(\frac{I_{D0}}{I_s}\right)$$

$$I_{D0} = I_s e^{v_{DN}/V_t} \text{ by division}$$

Graphical Model



Iterative Model

use Exp Model formulas and Repeat for accuracy

Constant Voltage drop Model $\rightarrow V_0 = 0.7V$

Ideal Diode $\rightarrow V_0 = 0V$

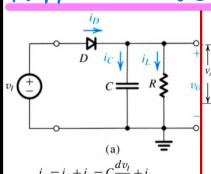
$\rightarrow I_{D0} > 0A$

Small-signal Model

$$i_o(t) = I_{D0} e^{v_{DN}/V_t} \rightarrow \frac{v_o}{V_t} \ll 1$$

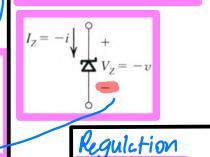
$$i_A = \frac{v_A}{i_D} = \frac{V_A}{I_{D0}}$$

Ripple Voltage



Zener Diodes

$$V_Z = V_{Z0} + r_z I_Z$$



Regulation

$$\text{Line: } \Delta V_o / \Delta V_i \\ \text{Load: } \Delta V_o / \Delta I_L$$

Filters

$$T = R C \quad I_L = V_{avg}/R$$

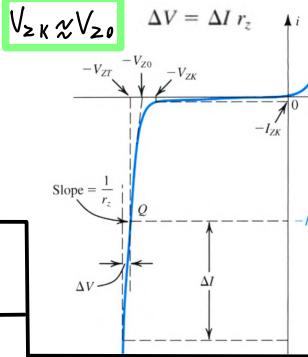
During diode off: $v_o = V_p e^{-t/V_T}$

$$I_L = V_s (1 - e^{-t/V_T}) / R$$

$$V_r \approx V_p T / R \rightarrow \text{assume } e^{-t/V_T} = 1 - t / V_T$$

$$V_r = V_p / T R C = I_L / R C$$

$$V_Z \approx V_{Z0}$$



IL PIV/Vbreak Rectifiers

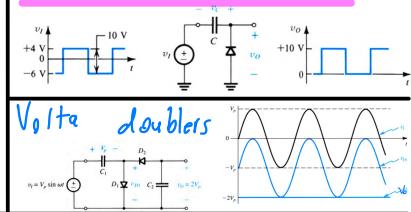
Half-wave	V_{avg}/R_L	V_s
Full-wave	V_{avg}/R_L	$2V_s - V_b$
Bridge	V_{avg}/R_L	$V_s - V_b$

$$V_s = \text{Source Voltage}$$

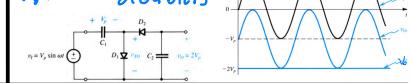
$$V_{avg} = \text{Avg Output}$$

$$L = \frac{2}{\pi} \frac{V_p}{V_s}$$

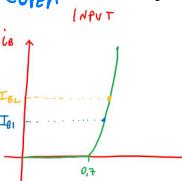
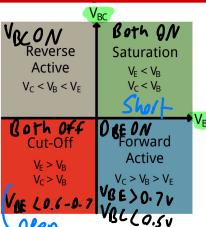
Clamped capacitor, DC Restorer



Volta doublers



BJT's Always Check Operation Mode



Find operation mode, I, V

$\beta = 100$

$V_B = 10 - 0.7 = 9.3V$

$I_B = \frac{9.3}{390k} = 23.8 \mu A$

$I_C = 100 \cdot 23.8 \mu A = 2.38mA = I$

$V_C = 2.38mA \cdot 2.2k = 5.24V = V$

$V_{CB} = 5.24 - 9.3V < 0.5V$ Active region

PNP

ACTIVE

$$i_c = I_s e^{v_{BE}/V_t} = I_c + I_e \frac{V_E}{V_t}$$

$$i_B = \frac{i_c}{\beta} = \left(\frac{1}{\alpha}\right) e^{v_{BE}/V_t}$$

$$i_E = \frac{i_c}{\alpha} = \left(\frac{1}{\beta}\right) e^{v_{BE}/V_t}$$

Note: For the pnp transistor, replace v_{BE} with v_{EB} .

$$i_c = \alpha i_E$$

$$i_c = \beta i_B$$

$$\beta = 1 - \alpha$$

$$i_B = (1 - \alpha) i_E = \frac{i_c}{\beta + 1}$$

$$i_E = (\beta + 1) i_B = i_c + \beta i_c$$

$$\alpha = \frac{\beta}{\beta + 1}$$

INPUT i_A

OUTPUT i_C

SATURATION $i_{C0} = \beta \cdot i_{B0}$

ACTIVE $i_{C0} = \beta \cdot i_{B0}$

$I_3 = \frac{0.7}{33k} = 21.2 \mu A$

$I_3 = \frac{I_c}{\beta} = 0.02 I_c$

$I_2 = I_3 + I_2 = 21.2 \mu A + 0.02 I_c$

$I_1 = I_c + I_2 = I_c + 21.2 \mu A + 0.02 I_c$

KVL loop ① $I_0 = I_1 \cdot 10k + I_2 \cdot 100k + 0.7$

$I_0 = (I_c + 21.2 \mu A + 0.02 I_c) \cdot 10k + (21.2 \mu A + 0.02 I_c) \cdot 100k + 0.7$

$$\text{Solve for } I_c \rightarrow I_c = 0.571 \mu A$$

$$I_i = 582 \mu A + 21.2 \mu A = 603.2 \mu A$$

$$V_C = 10 - 603.2 \mu A \cdot 10k = 3.96 \gg V_B$$

$$V_{CE} = V_C$$

How to Thevenin

$$15V \xrightarrow{200k} \xrightarrow{10k} V_{BB} = 15 \left(\frac{10k}{100k + 10k} \right) = 5V$$

$$R_B = 200k // 10k = 66.7k\Omega$$

Do KVL

$I_E = (\beta + 1) I_B$

$V_{BB} = V_{BB} \Big|_{V=0} + \frac{V_{BB} - V_E}{10k}$

$V_{AB} \Big|_{V=0} = 15 \cdot \frac{1m}{470k + 1m} = 10.2V$

$V_{AB} \Big|_{V=0} = -15 \cdot \frac{1m}{470k + 1m} = -4.8V$

Active region

$V_{BB} = 10.2 - 4.8 = 5.4V$

$R_B = 470k // 1m = 360k\Omega$

$I_B = \frac{5.4 - 0.7}{320k} = 14.7 \mu A$

Bjt Amplifiers | CE \rightarrow T T or CC \rightarrow T

How to Solve Bjt amp's

Common Base Configuration - has Voltage Gain but no Current Gain.

Common Emitter Configuration - has both Current and Voltage Gain.

Common Collector Configuration - has Current Gain but no Voltage Gain.

1. Eliminate the signal source and determine the dc operating point of the transistor.
2. Calculate the values of the parameters of the small-signal model.
3. Eliminate the dc sources by replacing each dc voltage source by a short circuit and each dc current source by an open circuit.
4. Replace the transistor with one of its small-signal equivalent-circuit models. Although any of the models can be used, one might be more convenient than the others for the particular circuit being analyzed. This point is made clearer in Section 7.3.
5. Analyze the resulting circuit to determine the required quantities (e.g., voltage gain, input resistance).

Table 7.5 Characteristics of BJT Amplifiers^{a,c} $A_{vB} = A_V = V_o/V_i / R_i = \text{parallel add}$

	R_{in}	A_{in}	R_o	A_v	$G_v \text{ gain}$
Common emitter (Fig. 7.37)	$(\beta + 1)r_e$	$-g_m R_C$	R_C	$-g_m (R_C R_L)$ $- \frac{R_C R_L}{r_e + R_C}$	$-\beta \frac{R_C R_L}{R_{in} + (\beta + 1)r_e}$
Common emitter with R_e (Fig. 7.39)	$(\beta + 1)(r_e + R_e)$	$-\frac{g_m R_C}{1 + g_m R_e}$	R_C	$-g_m (R_C R_L)$ $- \frac{R_C R_L}{1 + g_m R_e + r_e + R_e}$	$-\beta \frac{R_C R_L}{R_{in} + (\beta + 1)(r_e + R_e)}$
Common base (Fig. 7.41)	r_e	$g_m R_C$	R_C	$g_m (R_C R_L)$ $\alpha \frac{R_C R_L}{r_e}$	$\alpha \frac{R_C R_L}{R_{in} + r_e}$
Emitter follower (Fig. 7.44) CC	$(\beta + 1)(r_e + R_L)$	1	r_e	$\frac{R_L}{R_L + r_e}$	$\frac{R_L}{R_L + r_e + R_{in}/(\beta + 1)}$
				$G_{vo} = 1$	
				$R_{out} = r_e + \frac{R_{in}}{\beta + 1}$	

^a For the interpretation of A_{in} , A_{in} , and r_e refer to Fig. 7.35.

^b The BJT output resistance r_o is not taken into account in these formulas.

^c Setting $\beta = \infty$ ($\alpha = 1$) and replacing r_e with $1/g_m$, R_C with R_D , and R_o with R_t results in the corresponding formulas for MOSFET amplifiers (Section 7.4).

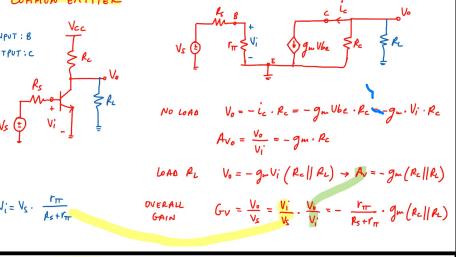
$$i_B = \frac{I_C}{\beta} + \frac{i_C}{\beta}$$

$$V_T = V_{BE}$$

$$i_E = \frac{I_C}{\alpha} + \frac{i_C}{\alpha}$$

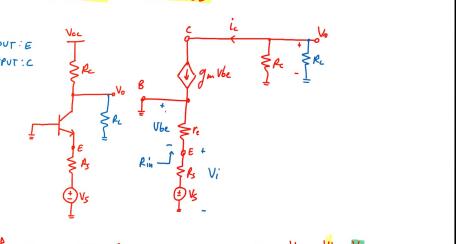
CURRENT AMPLIFICATION

COMMON Emitter



CURRENT AMPLIFICATION

COMMON BASE



CURRENT AMPLIFICATION

COMMON COLLECTOR

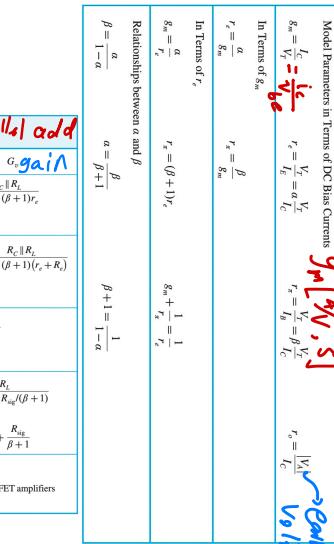
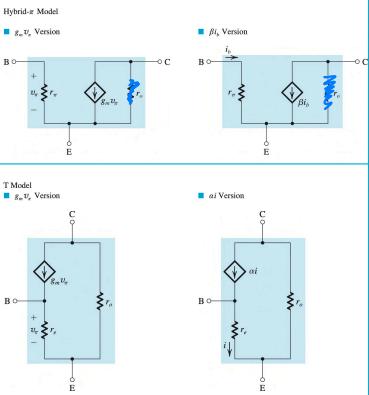


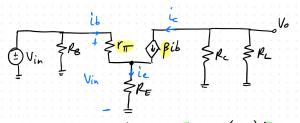
Table 7.3 Small-Signal Models of the BJT



Consider the common emitter amplifier in Figure 3.

- Derive an expression of the voltage gain $A_v = V_o/V_i$ in terms of r_{π} and β .
- Assume that $\beta = 100$, $V_{BE} = 0.7$, $R_E = 2k\Omega$, $R_C = 2k\Omega$, $R_{in} = 100\Omega$ and $V_{CC} = 20V$. Determine the required value of R_E so that $I_C = 5mA$.

(a) Expression of A_v in terms of $r_{\pi} \times \beta$ requires the use of T-model



$$V_{in} = i_B \cdot R_E + i_E \cdot R_E = (1 + \beta) i_B \cdot R_E$$

$$V_o = i_C (R_L || R_C) = -\beta i_B (R_L || R_C)$$

$$\boxed{A_v = -\frac{V_o}{V_{in}} = \frac{\beta}{(R_L || R_C) + R_E}}$$

$$A_v = -\frac{V_o}{V_{in}} = -\frac{\beta (R_L || R_C)}{R_E + \beta (R_L || R_C)}$$

$$\boxed{A_v = -\frac{V_o}{V_{in}} = -\frac{\beta (R_L || R_C)}{R_E + (\beta + 1) R_E}}$$

To have $I_C = 5mA$

$$I_E = \frac{1}{100} = 50\mu A$$

$$I_E = 5mA + 50\mu A = 5.05mA$$

$$V_B = 5.05mA \cdot 100 = 0.5V$$

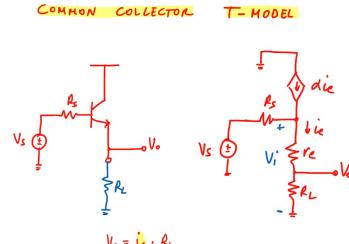
$$V_B = 0.5 + 0.7 = 1.2V$$

$$R_E = \frac{20 - 1.2}{50\mu A} = 37.6k\Omega$$

$$V_{CC} = 20 - 5m \cdot 2k = 10V$$

$$V_{BC} = 1.2 - 10 < 0.5V$$

Active region



$$V_o = i_C \cdot R_L$$

$$i_C = \frac{V_i - V_o}{R_E} = \frac{V_i}{R_E} - \frac{V_o}{R_E}$$

$$V_o = V_i \frac{R_L}{R_E} - V_o \frac{R_L}{R_E}$$

$$A_v = \frac{V_o}{V_i} = \frac{R_L}{R_E + R_L}$$

$$R_E \gg R_L \rightarrow A_v = 1$$

$$\text{Otherwise } A_v < 1$$

